# **UNR7231** (UN7231)

## Silicon NPN epitaxial planar type

#### For low-frequency amplification

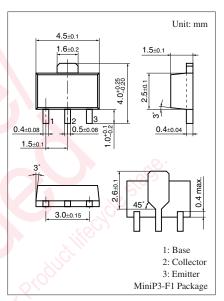
#### ■ Features

- High forward current transfer ratio h<sub>FE</sub>
- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.

### ■ Absolute Maximum Ratings $T_a = 25$ °C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	20	V	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	20	V	
Collector current	$I_{C}$	0.7	A	
Peak collector current	$I_{CP}$	1.5	A	
Total power dissipation *	$P_{T}$	1.0	W	
Junction temperature	$T_{j}$	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

Note) \*: Printed circuit board: Copper foil area of 1 cm<sup>2</sup> or more, and the board thickness of 1.7 mm for the collector portion



Marking Symbol: IC

#### Internal Connection

$$\begin{array}{c}
R_{1}(1 \text{ k}\Omega) \\
\text{Bo-WV} \\
R_{2} \\
(47 \text{ k}\Omega)
\end{array}$$

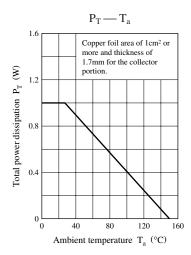
## ■ Electrical Characteristics $T_a = 25$ °C $\pm 3$ °C

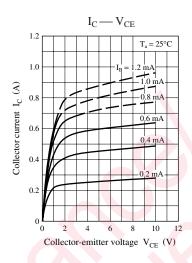
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	$V_{CBO}$	$I_{\rm C} = 10 \; \mu A, I_{\rm E} = 0$	20			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_C = 1 \text{ mA}, I_B = 0$	20			V
Collector-base cutoff current (Emitter open)	$I_{CBO}$	$V_{CB} = 15 \text{ V}, I_{E} = 0$			1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 15 \text{ V}, I_{B} = 0$			10	μΑ
Emitter-base cutoff current (Collector open)	$I_{EBO}$	$V_{EB} = 14 \text{ V}, I_C = 0$			0.5	mA
Forward current transfer ratio *	$h_{FE}$	$V_{CE} = 10 \text{ V}, I_{C} = 150 \text{ mA}$	800		2100	
Collector-emitter saturation voltage *	V <sub>CE(sat)</sub>	$I_C = 500 \text{ mA}, I_B = 5 \text{ mA}$			0.4	V
Input resistance	R <sub>1</sub>	0/8° //	0.7	1.0	1.3	kΩ
Resistance ratio	R <sub>1</sub> /R <sub>2</sub>		0.016	0.021	0.025	
Transition frequency	$f_T$	$V_{CB} = 20 \text{ V}, I_E = -20 \text{ mA}, f = 200 \text{ MHz}$		55		MHz

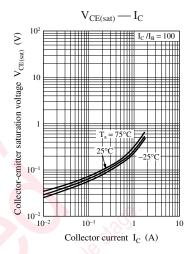
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

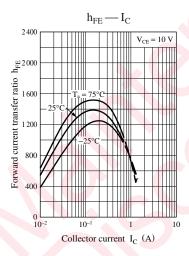
2. \*: Pulse measurement

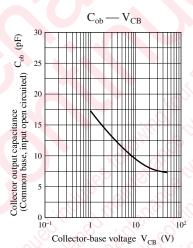
Note) The part number in the parenthesis shows conventional part number.











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